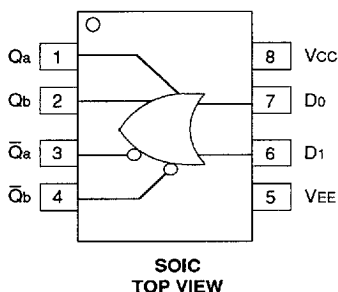


FEATURES

- 290ps propagation delay
- Dual outputs for 25Ω drive applications
- Internal 75KΩ Input pull-down resistors
- ESD protection of 2000V

PIN CONFIGURATION/BLOCK DIAGRAM



DESCRIPTION

The SY10EL/100EL12 are low-impedance drive buffers. With two pairs of OR/NOR outputs, the devices are ideally suited for high drive applications such as memory addressing. These devices are functionally equivalent to the E112 devices, with higher performance capabilities. With propagation delays significantly faster than the E112, the EL12 is ideally suited for those applications which require the ultimate in AC performance.

PIN NAMES

Pin	Function
D0, D1	Data Inputs
Qa, Qb	Data Outputs

PRODUCT ORDERING CODE

Ordering Code	Package Type	Operating Range
SY10EL12ZC	Z8-1	Commercial
SY100EL12ZC	Z8-1	Commercial

DC ELECTRICAL CHARACTERISTICS

VEE = VEE (Min.) to VEE (Max.); VCC = GND

Symbol	Parameter	-40°C			0°C			+25°C			+85°C			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
IEE	Power Supply Current													mA
	10EL	—	14	—	11	14	17	11	14	17	11	14	17	
	100EL	—	14	—	11	14	17	11	14	17	13	16	20	
VEE	Power Supply Voltage													V
	10EL	-4.94	-5.2	-5.5	-4.94	-5.2	-5.5	-4.94	-5.2	-5.5	-4.94	-5.2	-5.5	
	100EL	-4.20	-4.5	-5.5	-4.20	-4.5	-5.5	-4.20	-4.5	-5.5	-4.20	-4.5	-5.5	
I _{IH}	Input HIGH Current	—	—	150	—	—	150	—	—	150	—	—	150	μA

AC ELECTRICAL CHARACTERISTICS

VEE = VEE (Min.) to VEE (Max.); VCC = GND

Symbol	Parameter	-40°C			0°C			+25°C			+85°C			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
t _{PLH} t _{PHL}	Propagation Delay to Output D	—	280	—	170	280	450	180	290	450	210	320	480	ps
t _r t _f	Output Rise/Fall Times Q (20% to 80%)	—	350	—	150	350	550	150	350	550	150	350	550	ps